



10NM65-U2

Power MOSFET

10A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

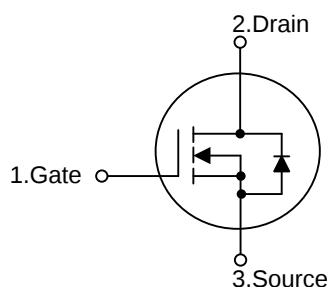
DESCRIPTION

The UTC 10NM65-U2 is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 0.58\Omega$ @ $V_{GS}=10V$, $I_D=5.0A$
- * By using Super Junction Structure
- * Fast Switching
- * With 100% Avalanche Tested

SYMBOL

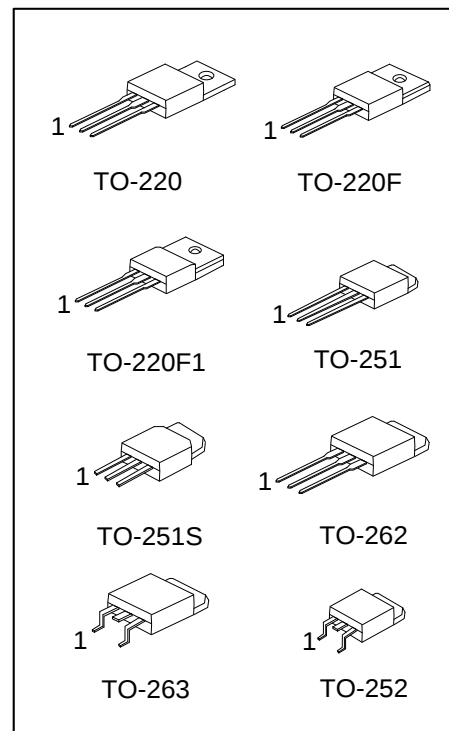


ORDERING INFORMATION

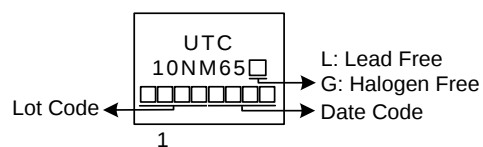
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10NM65L-TA3-T	10NM65G-TA3-T	TO-220	G	D	S	Tube
10NM65L-TF3-T	10NM65G-TF3-T	TO-220F	G	D	S	Tube
10NM65L-TF1-T	10NM65G-TF1-T	TO-220F1	G	D	S	Tube
10NM65L-TM3-T	10NM65G-TM3-T	TO-251	G	D	S	Tube
10NM65L-TMS-T	10NM65G-TMS-T	TO-251S	G	D	S	Tube
10NM65L-TN3-R	10NM65G-TN3-R	TO-252	G	D	S	Tape Reel
10NM65L-T2Q-T	10NM65G-T2Q-T	TO-262	G	D	S	Tube
10NM65L-TQ2-T	10NM65G-TQ2-T	TO-263	G	D	S	Tube
10NM65L-TQ2-R	10NM65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

10NM65G-TA3-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F TM3: TO-251, TMS: TO-251S, TN3: TO-252, T2Q: TO-262, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
--	--



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	650	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	10	A
	Pulsed (Note 2)	I _{DM}	20	A
Avalanche Current (Note 2)		I _{AR}	1.9	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	312	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5.6	V/ns
Power Dissipation	TO-220/TO-262/TO-263	P _D	78	W
	TO-220F/TO-220F1		25	W
	TO-251/TO-251S		52	W
	TO-252			
Junction Temperature		T _J	+150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. L=100mH, I_{AS}=2.5A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C

4. I_{SD} ≤10A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^{\circ}\text{C/W}$
	TO-220F1/TO-262			
	TO-263		110	
TO-251/TO-251S				
	TO-252			
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	1.6	$^{\circ}\text{C/W}$
	TO-220F/TO-220F1		5.0	
	TO-251/TO-251S		2.4 (Note)	
	TO-252			

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

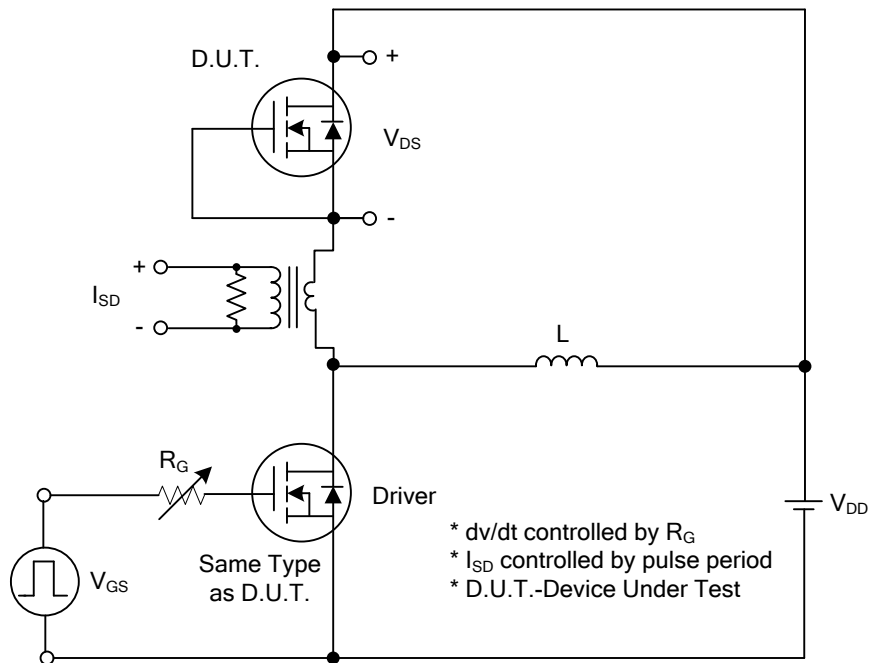
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{DS} =0V ,V _{GS} =30V			100	nA
	Reverse		V _{DS} =0V ,V _{GS} =-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D =250μA	2.5		4.5	V
Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =5.0A			0.58	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		610		pF
Output Capacitance		C _{OSS}			500		pF
Reverse Transfer Capacitance		C _{RSS}			40		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =520V, V _{GS} =10V, I _D =10A, I _G =1mA (Note 1, 2)		27		nC
Gate to Source Charge		Q _{GS}			9.2		nC
Gate to Drain Charge		Q _{GD}			7.5		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =10A, R _G =25Ω (Note 1, 2)		8		ns
Rise Time		t _R			21		ns
Turn-OFF Delay Time		t _{D(OFF)}			63		ns
Fall-Time		t _F			36		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				10	A
Maximum Body-Diode Pulsed Current		I _{SM}				20	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =10A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =10A, V _{GS} =0V,		380		ns
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		5		μC

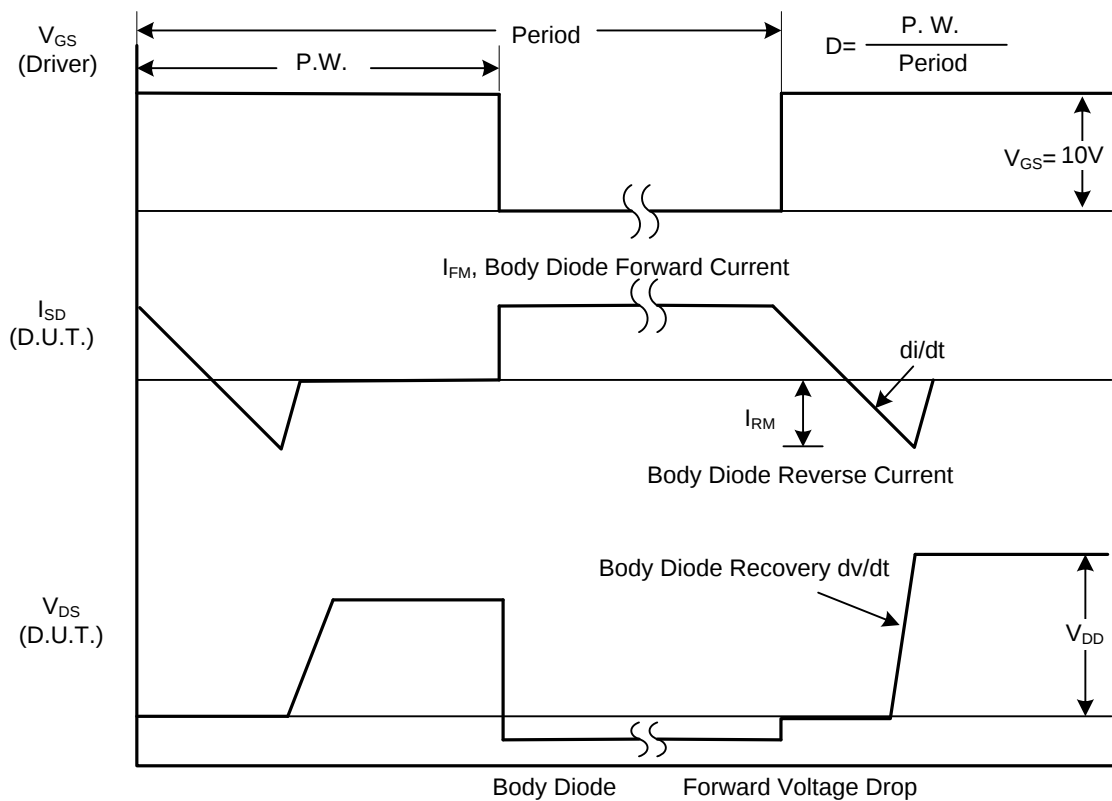
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

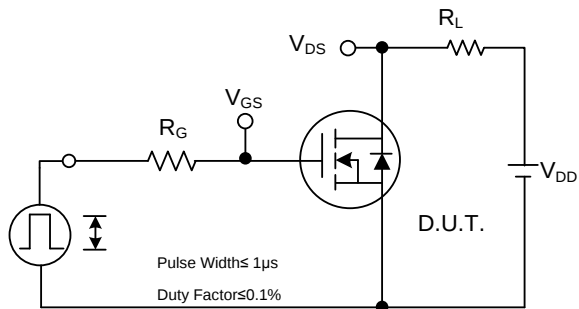


Peak Diode Recovery dv/dt Test Circuit

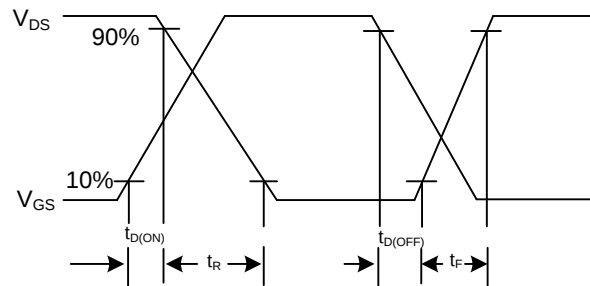


Peak Diode Recovery dv/dt Waveforms

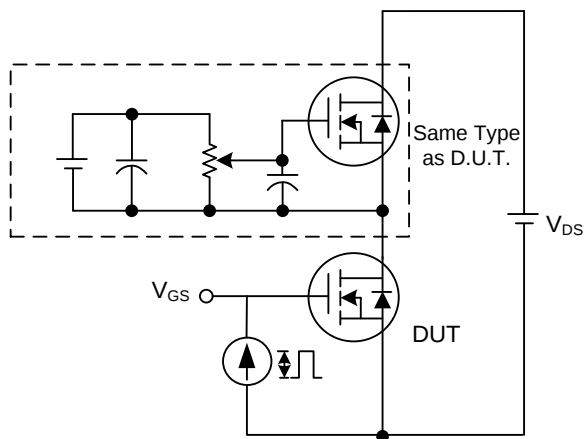
■ TEST CIRCUITS AND WAVEFORMS



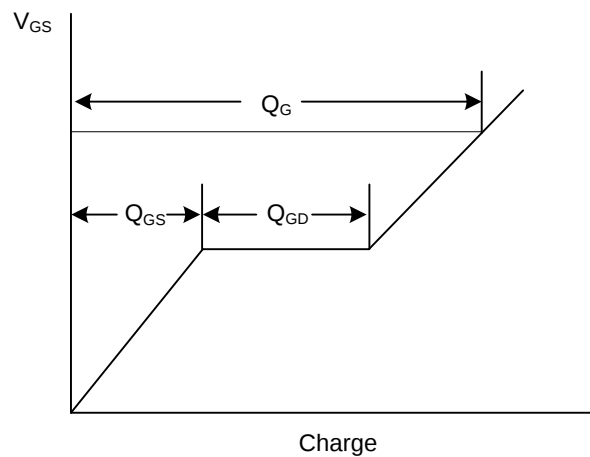
Switching Test Circuit



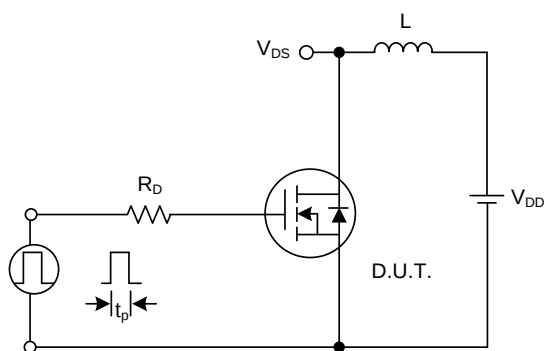
Switching Waveforms



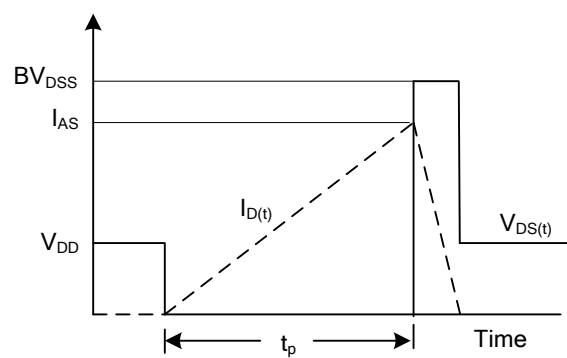
Gate Charge Test Circuit



Gate Charge Waveform

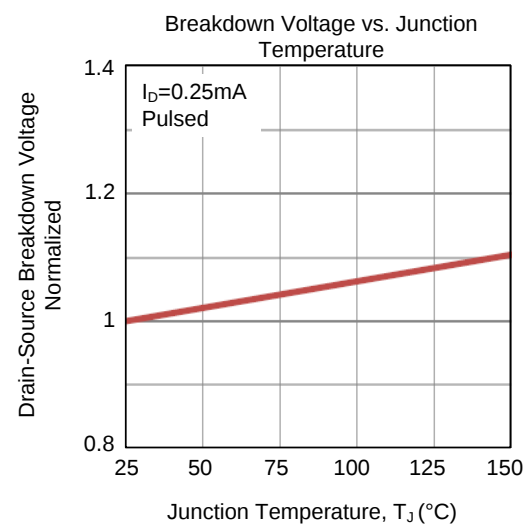
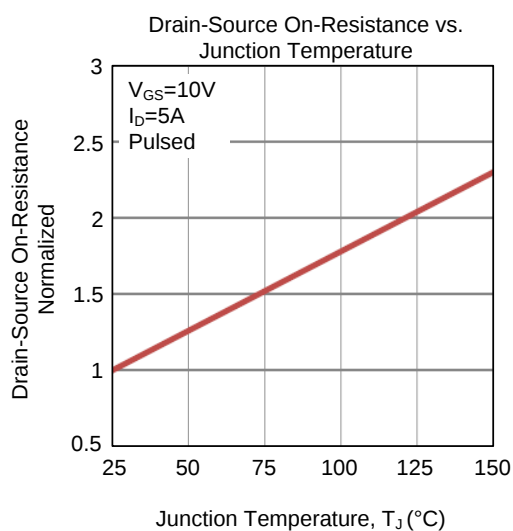
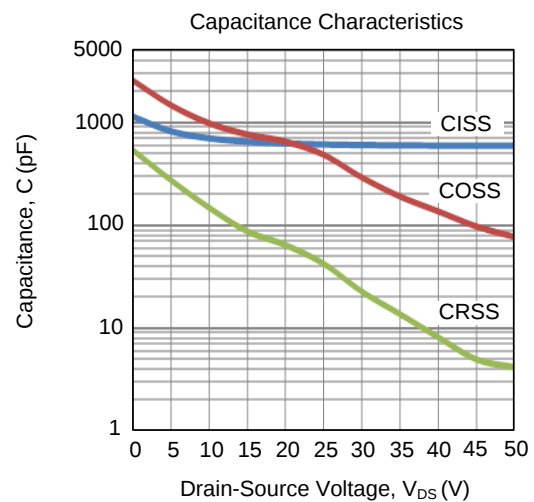
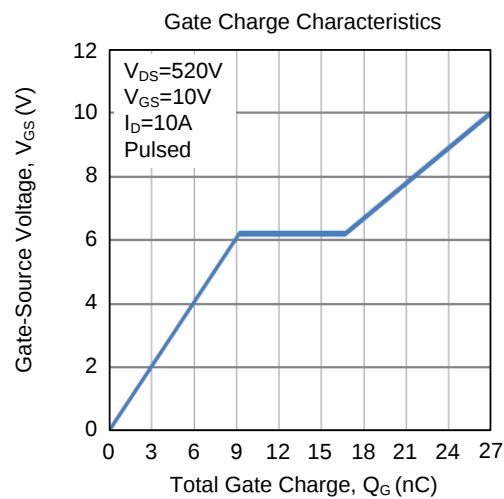
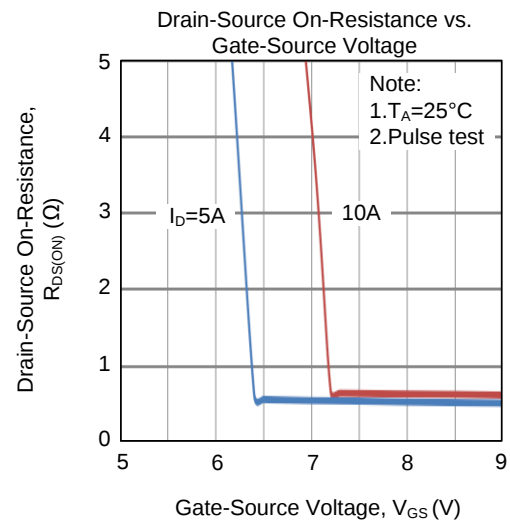
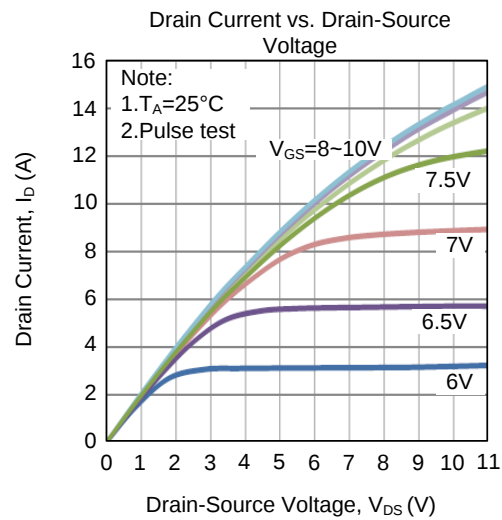


Unclamped Inductive Switching Test Circuit

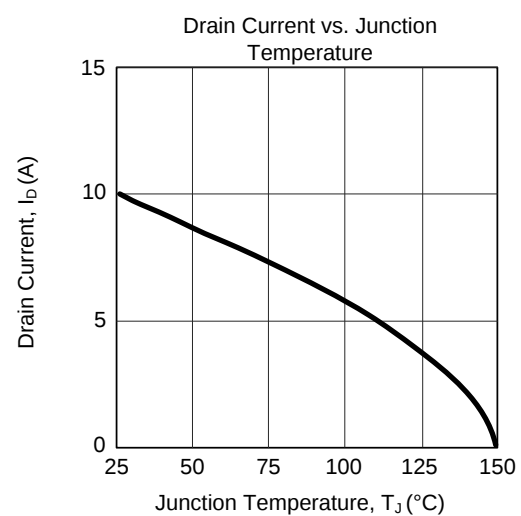
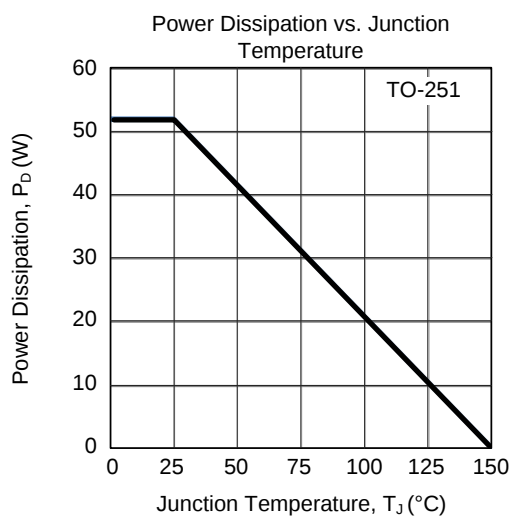
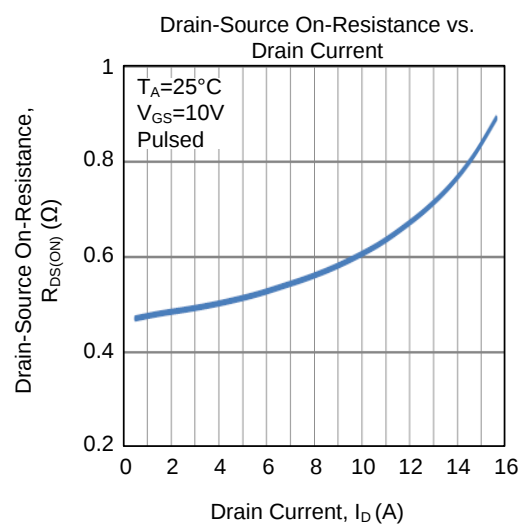
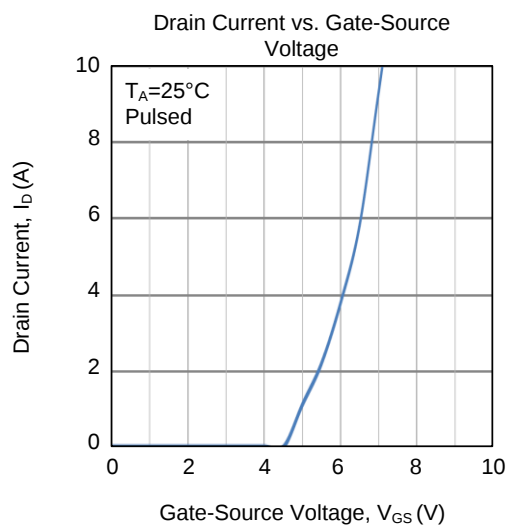
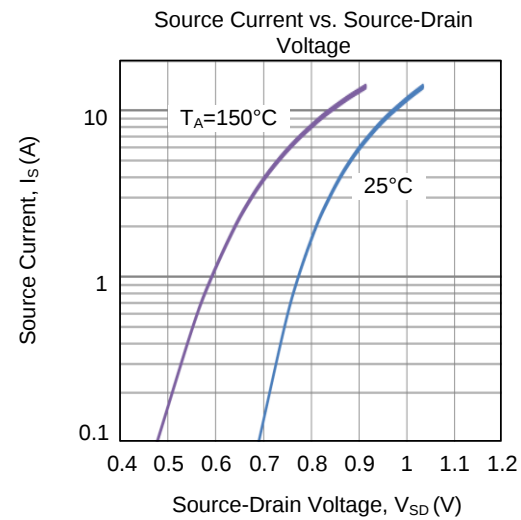
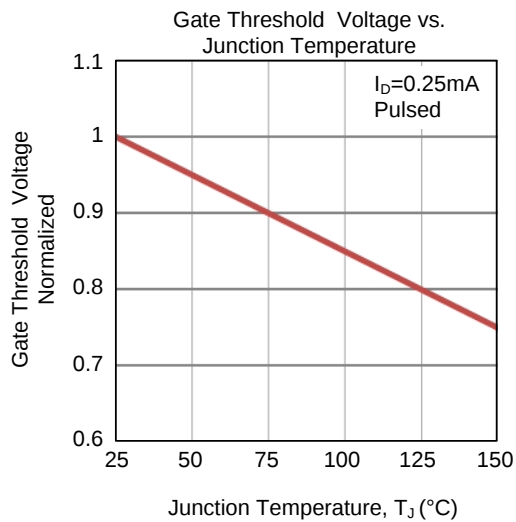


Unclamped Inductive Switching Waveforms

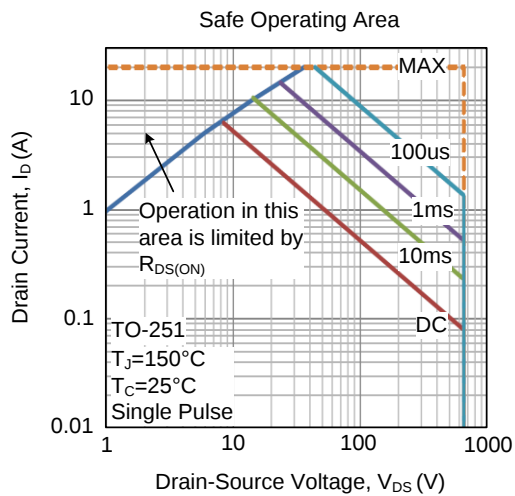
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.